

Silicon Standard Recovery Diode

 $V_{RRM} = 600\text{ V} - 1600\text{ V}$
 $I_F = 150\text{ A}$

Features

- High Surge Capability
- Types up to 1600 V V_{RRM}

Three Tower Package


Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	MSRT150120(A)	MSRT150140(A)	MSRT150160(A)	Unit
Repetitive peak reverse voltage	V_{RRM}		1200	1400	1600	V
RMS reverse voltage	V_{RMS}					V
DC blocking voltage	V_{DC}					V
Continuous forward current	I_F					A
Operating temperature	T_j					°C
Storage temperature	T_{stg}					°C

Parameter	Symbol	MSRT150140(A)	Unit
Diode forward voltage			μA mA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}	0.	°C/W
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